

Single Diode

# Schottky Barrier Diode

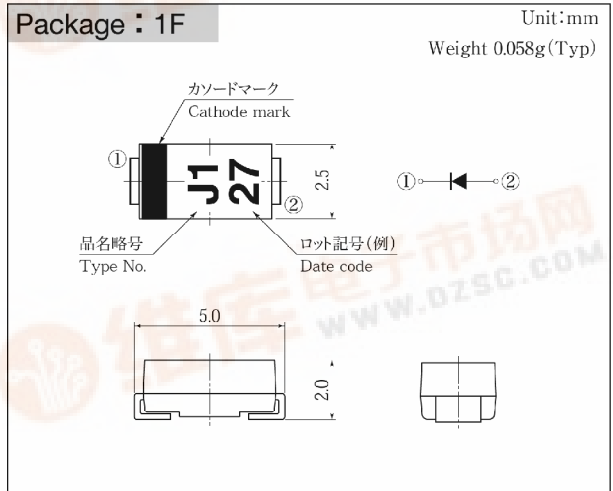
## D1FJ10

### 100V 1A

- |              |                |
|--------------|----------------|
| <b>特長</b>    | <b>Feature</b> |
| ● 小型SMD      | ● Small SMD    |
| ● Tj=150°C   | ● Tj=150°C     |
| ● 低Ir= 0.2mA | ● Low Ir=0.2mA |

- |                |                                           |
|----------------|-------------------------------------------|
| <b>用途</b>      | <b>Main Use</b>                           |
| ● スイッチング電源     | ● Switching Regulator                     |
| ● DC/DC コンバータ  | ● DC/DC Converter                         |
| ● 家電、ゲーム、OA 機器 | ● Home Appliance, Game, Office Automation |
| ● 通信、ポータブル機器   | ● Communication, Portable set             |

### ■外観図 OUTLINE



外形図については新電元Webサイト又は〈ダイオードカタログ・技術資料編〉を参照下さい。捺印表示については捺印仕様をご確認下さい。  
For details of the outline dimensions, refer to our web site or the diode technical data book. As for the marking, refer to the specification "Marking, Terminal Connection".

### ■定格表 RATINGS

●絶対最大定格 Absolute Maximum Ratings (指定のない場合 Tc = 25°C)

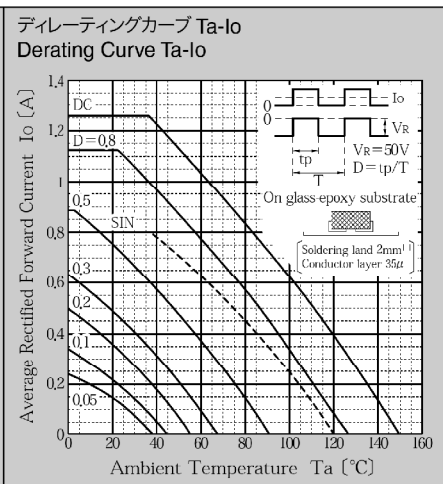
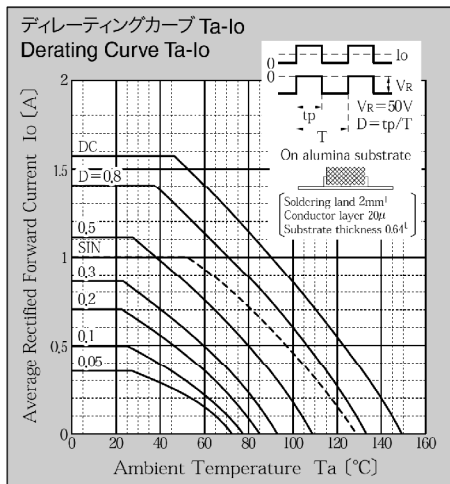
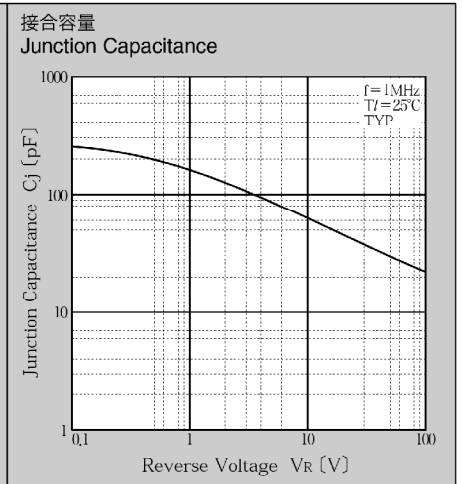
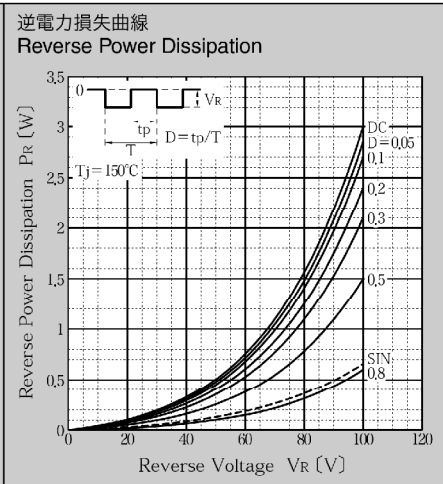
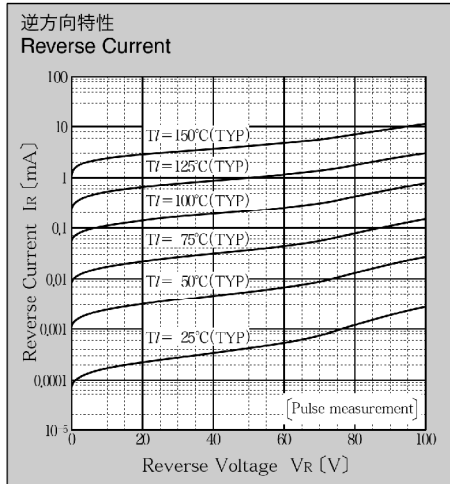
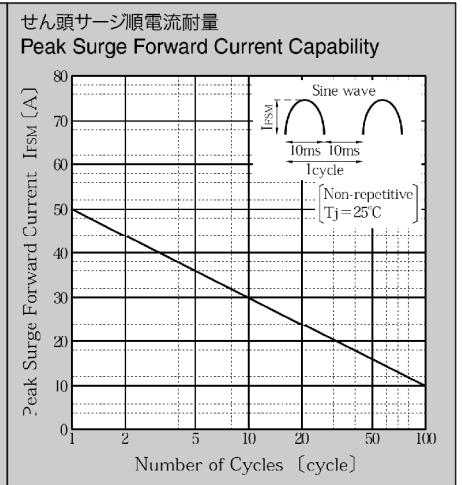
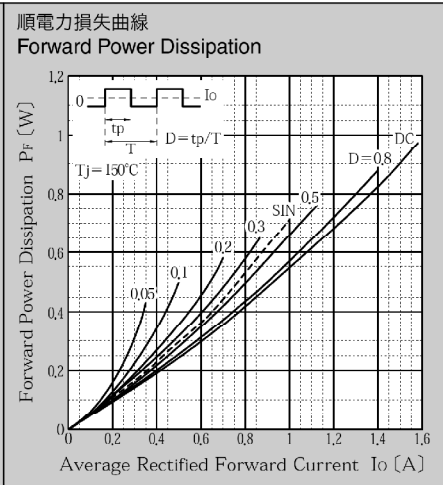
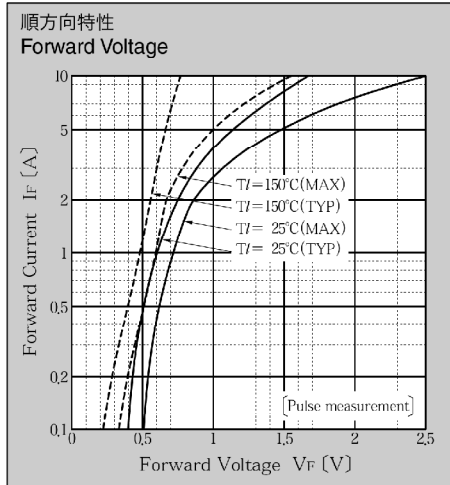
| 項目<br>Item                                | 記号<br>Symbol     | 条件<br>Conditions                                                                                    | 品名<br>Type No.                                 | D1FJ10  | 単位<br>Unit |
|-------------------------------------------|------------------|-----------------------------------------------------------------------------------------------------|------------------------------------------------|---------|------------|
| 保存温度<br>Storage Temperature               | Tstg             |                                                                                                     |                                                | -55~150 | °C         |
| 接合部温度<br>Operation Junction Temperature   | Tj               |                                                                                                     |                                                | 150     | °C         |
| せん頭逆電圧<br>Maximum Reverse Voltage         | V <sub>RM</sub>  |                                                                                                     |                                                | 100     | V          |
| 出力電流<br>Average Rectified Forward Current | I <sub>O</sub>   | 50Hz 正弦波, 抵抗負荷<br>50Hz sine wave, Resistance load                                                   | Ta = 52°C アルミナ基板実装<br>On alumina substrate     | 1.00    | A          |
|                                           |                  |                                                                                                     | Ta = 36°C プリント基板実装<br>On glass-epoxy substrate | 0.8     |            |
| せん頭サージ順電流<br>Peak Surge Forward Current   | I <sub>FSM</sub> | 50Hz 正弦波, 非繰り返し1サイクルせん頭値, Tj = 25°C<br>50Hz sine wave, Non-repetitive 1 cycle peak value, Tj = 25°C |                                                | 50      | A          |

●電氣的・熱的特性 Electrical Characteristics (指定のない場合 Tl = 25°C)

|                                      |                 |                                                               |                                  |      |
|--------------------------------------|-----------------|---------------------------------------------------------------|----------------------------------|------|
| 順電圧<br>Forward Voltage               | V <sub>F</sub>  | I <sub>F</sub> = 1.0A, パルス測定<br>Pulse measurement             | MAX 0.72                         | V    |
| 逆電流<br>Reverse Current               | I <sub>R</sub>  | V <sub>R</sub> = V <sub>RM</sub> , パルス測定<br>Pulse measurement | MAX 0.2                          | mA   |
| 接合容量<br>Junction Capacitance         | C <sub>j</sub>  | f = 1MHz, V <sub>R</sub> = 10V                                | TYP 63                           | pF   |
| 熱抵抗<br>Thermal Resistance            | θ <sub>jl</sub> | 接合部・リード間<br>Junction to lead                                  | MAX 23                           | °C/W |
|                                      | θ <sub>ja</sub> | 接合部・周囲間<br>Junction to ambient                                | アルミナ基板実装<br>On alumina substrate |      |
| プリント基板実装<br>On glass-epoxy substrate |                 |                                                               | MAX 157                          |      |



■特性図 CHARACTERISTIC DIAGRAMS



\* Sine waveは50Hzで測定しています。  
\* 50Hz sine wave is used for measurements.  
\* 半導体製品の特性は一般的にバラツキを持っており、Typicalは統計的な実力を表しています。  
\* Semiconductor products generally have characteristic variation. Typical is a statistical average of the device's ability.